

Konstantin Zhuravlev

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210
papers

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231
ext. papers

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ext. citations

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avg, IF

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L-index

#	Paper	IF	Citations
210	Self-trapped exciton recombination in silicon nanocrystals. <i>Physical Review B</i> , 2001 , 63,	3.3	82
209	Mechanism of photoluminescence of Si nanocrystals fabricated in a SiO ₂ matrix. <i>Applied Physics Letters</i> , 1998 , 73, 2962-2964	3.4	48
208	Atomic and energy structure of InAs/AlAs quantum dots. <i>Physical Review B</i> , 2008 , 78,	3.3	42
207	Interplay of exciton and electron-hole plasma recombination on the photoluminescence dynamics in bulk GaAs. <i>Physical Review B</i> , 2006 , 73,	3.3	37
206	Effect of surface acoustic waves on low-temperature photoluminescence of GaAs. <i>Applied Physics Letters</i> , 1997 , 70, 3389-3391	3.4	36
205	Exciton recombination dynamics in an ensemble of (In,Al)As/AlAs quantum dots with indirect band-gap and type-I band alignment. <i>Physical Review B</i> , 2011 , 84,	3.3	30
204	The origin of 2.7 eV blue luminescence band in zirconium oxide. <i>Journal of Applied Physics</i> , 2014 , 116, 244109	2.5	29
203	Photoluminescence of high-quality AlGaAs layers grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2000 , 76, 1131-1133	3.4	23
202	Prospects for the development of high-power field-effect transistors based on heterostructures with donor-acceptor doping. <i>Semiconductors</i> , 2014 , 48, 666-674	0.7	21
201	Millisecond photoluminescence kinetics in a system of direct-bandgap InAs quantum dots in an AlAs matrix. <i>JETP Letters</i> , 2003 , 77, 389-392	1.2	21
200	Electron scattering in AlGa _N /Ga _N heterostructures with a two-dimensional electron gas. <i>Semiconductors</i> , 2013 , 47, 33-44	0.7	19
199	Carrier dynamics in InAs/AlAs quantum dots: lack in carrier transfer from wetting layer to quantum dots. <i>Nanotechnology</i> , 2010 , 21, 155703	3.4	19
198	Changes in optical properties of CdS nanoclusters in langmuir-blodgett films on passivation in ammonia. <i>Semiconductors</i> , 2008 , 42, 702-709	0.7	16
197	Photoluminescence from cadmium sulfide nanoclusters formed in the matrix of a Langmuir-Blodgett film. <i>Semiconductors</i> , 2003 , 37, 1321-1325	0.7	16
196	Characterization of MBE-grown AlGa _N layers heavily doped using silane. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 315-318		15
195	Excitonic polaritons in semiconductor solid solutions Al _x Ga _{1-x} As. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 900-905		15
194	Liquid phase epitaxial growth of undoped gallium arsenide from bismuth and gallium melts. <i>Crystal Research and Technology</i> , 1989 , 24, 235-246	1.3	15

193	The influence of irradiation and subsequent annealing on Si nanocrystals formed in SiO ₂ layers. <i>Semiconductors</i> , 2000 , 34, 965-970	0.7	14
192	Recombination of self-trapped excitons in silicon nanocrystals grown in silicon oxide. <i>Semiconductors</i> , 2000 , 34, 1203-1206	0.7	14
191	Luminescence and superradiance in electron-beam-excited Al _x Ga _{1-x} N. <i>Journal of Applied Physics</i> , 2014 , 116, 113103	2.5	13
190	Decreasing the role of transverse spatial electron transport and increasing the output power of heterostructure field-effect transistors. <i>Technical Physics Letters</i> , 2012 , 38, 819-821	0.7	13
189	Spin relaxation of negatively charged excitons in (In,Al)As/AlAs quantum dots with indirect band gap and type-I band alignment. <i>Applied Physics Letters</i> , 2012 , 101, 142108	3.4	13
188	Strong sensitivity of photoluminescence of InAs/AlAs quantum dots to defects: evidence for lateral inter-dot transport. <i>Semiconductor Science and Technology</i> , 2006 , 21, 527-531	1.8	13
187	Synthesis of silicon oxide nanowires by the GJ EBP CVD method using different diluent gases. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 1774-1782	1.6	13
186	Photoluminescence dynamics in GaAs along an optically induced Mott transition. <i>Journal of Applied Physics</i> , 2007 , 101, 081717	2.5	12
185	Temperature dependence of photoluminescence of CdS nanoclusters formed in the Langmuir-Blodgett film matrix. <i>Semiconductors</i> , 2006 , 40, 1188-1192	0.7	12
184	Ge/Si waveguide photodiodes with built-in layers of Ge quantum dots for fiber-optic communication lines. <i>Semiconductors</i> , 2004 , 38, 1225-1229	0.7	12
183	Millisecond phosphorescence of free electrons in pure GaAs. <i>Applied Physics Letters</i> , 2001 , 79, 3455-3457	3.4	12
182	2D AlN crystal phase formation on (0001) Al ₂ O ₃ surface by ammonia MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 443-446		11
181	Effect of ion dose and annealing mode on photoluminescence from SiO ₂ implanted with Si ions. <i>Semiconductors</i> , 1998 , 32, 1222-1228	0.7	11
180	Pauli blockade of the electron spin flip in bulk GaAs. <i>Physical Review B</i> , 2007 , 75,	3.3	11
179	Influence of substrate temperature on the morphology of silicon oxide nanowires synthesized using a tin catalyst. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016 , 213, 1790-1795	1.6	10
178	Room temperature 1.5 μm light-emitting silicon diode with embedded FeSi ₂ nanocrystallites. <i>Applied Physics Letters</i> , 2012 , 101, 163501	3.4	10
177	Fluorinated Surface of Carbon Nanotube Bucky paper for Uniform Growth of CdS Nanoparticles. <i>Journal of Physical Chemistry C</i> , 2017 , 121, 19182-19190	3.8	9
176	Manganese-related recombination centers in epitaxial GaAs grown from a bismuth melt. <i>Semiconductors</i> , 1998 , 32, 43-48	0.7	9

175	Investigation of growth mechanisms of GaN quantum dots on (0001)AlN surface by ammonia MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 1548-1551		9
174	Influence of the additional p+ doped layers on the properties of AlGaAs/InGaAs/AlGaAs heterostructures for high power SHF transistors. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 095108	3	9
173	Electro- and Photoluminescence of CdS Nanoparticles Deposited on Carbon Nanotubes. <i>Journal of Nanoelectronics and Optoelectronics</i> , 2013 , 8, 36-41	1.3	8
172	Origin of the blue luminescence band in zirconium oxide. <i>Physics of the Solid State</i> , 2015 , 57, 1347-1351	0.8	7
171	Luminescence line shapes of band to deep centre and donor-acceptor transitions in AlN. <i>Journal of Physics Condensed Matter</i> , 2020 , 32, 435501	1.8	7
170	Growth of AlGaIn/GaN heterostructures with a two-dimensional electron gas on AlN/Al ₂ O ₃ substrates. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2013 , 49, 429-433	0.6	7
169	Electrical properties and deep traps spectra of N-polar and Ga-polar AlGaIn films grown by molecular beam epitaxy in a wide composition range. <i>Journal of Applied Physics</i> , 2009 , 105, 113712	2.5	7
168	Optical properties of photodetectors based on wurtzite quantum dot arrays. <i>Physical Review B</i> , 2008 , 77,	3.3	7
167	Deep levels and electron transport in AlGaIn/GaN heterostructures. <i>Semiconductors</i> , 2008 , 42, 52-58	0.7	7
166	Formation of nanocrystalline silicon films using high-dose H ⁺ ion implantation into silicon-on-insulator layers with subsequent rapid thermal annealing. <i>Semiconductors</i> , 2004 , 38, 107-112	0.7	7
165	Photoresistance of Si/Ge/Si structures with germanium quantum dots. <i>Semiconductors</i> , 2000 , 34, 1311-1315	1.5	7
164	Quantum-Sized Silicon Precipitates in Silicon-Implanted and Pulse-Annealed Silicon Dioxide Films: Photoluminescence and Structural Transformations. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 438, 453		7
163	High-Power High-Speed Schottky Photodiodes for Analog Fiber-Optic Microwave Signal Transmission Lines. <i>Technical Physics Letters</i> , 2019 , 45, 739-741	0.7	6
162	Chemical kinetics and thermodynamics of the AlN crystalline phase formation on sapphire substrate in ammonia MBE. <i>Journal of Thermal Analysis and Calorimetry</i> , 2018 , 133, 1099-1107	4.1	6
161	Thermodynamic and kinetic aspects of AlN crystal formation on (0001)Al ₂ O ₃ surface by ammonia MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 613-616		6
160	Electronic excitation energy transfer between CdS quantum dots and carbon nanotubes. <i>JETP Letters</i> , 2012 , 95, 362-365	1.2	6
159	Observation of the zero-magnetic-field exciton spin splitting in high quality bulk GaAs and AlGaAs. <i>Applied Physics Letters</i> , 2009 , 95, 182107	3.4	6
158	Wavelength-selective enhancement of the intensity of visible photoluminescence in hydrogen-ion-implanted silicon-on-insulator structures annealed under high pressure. <i>Applied Physics Letters</i> , 2006 , 89, 013106	3.4	6

157	Infrared light emission from GaAs MESFETs operating at avalanche breakdown conditions. <i>Semiconductor Science and Technology</i> , 2004 , 19, S94-S95	1.8	6
156	The role of nitrogen in the formation of luminescent silicon nanoprecipitates during heat treatment of SiO ₂ layers implanted with Si ⁺ ions. <i>Semiconductors</i> , 2001 , 35, 1182-1186	0.7	6
155	Characterization of shallow acceptors in GaAs by microsecond-scale time-resolved photoluminescence. <i>Applied Physics Letters</i> , 1996 , 68, 373-375	3.4	6
154	Photoluminescence kinetics in CdS nanoclusters formed by the Langmuir-Blodgett technique. <i>Semiconductors</i> , 2015 , 49, 380-386	0.7	5
153	Studying average electron drift velocity in pHEMT structures. <i>Technical Physics Letters</i> , 2016 , 42, 848-851	0.7	5
152	Decrease in the binding energy of donors in heavily doped GaN:Si layers. <i>Semiconductors</i> , 2014 , 48, 1134-1138	0.7	5
151	Increase in the diffusion length of minority carriers in Al _x Ga _{1-x} N alloys (x = 0.1) fabricated by ammonia molecular beam epitaxy. <i>Semiconductors</i> , 2015 , 49, 1285-1289	0.7	5
150	Quantum confinement and electron spin resonance characteristics in Si-implanted silicon oxide films. <i>Journal of Applied Physics</i> , 2011 , 109, 084502	2.5	5
149	Photoluminescence of GaN/AlN quantum dots at high excitation powers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 2230-2232		5
148	Influence of trapping on the exciton dynamics of Al _x Ga _{1-x} As films. <i>Applied Physics Letters</i> , 2005 , 86, 111906	3.4	5
147	Photoluminescence kinetics in GaAs under the influence of surface acoustic waves. <i>Semiconductors</i> , 2001 , 35, 895-899	0.7	5
146	Optical properties of germanium monolayers on silicon. <i>Semiconductors</i> , 2001 , 35, 941-946	0.7	5
145	Effect of the Sapphire-Nitridation Level and Nucleation-Layer Enrichment with Aluminum on the Structural Properties of AlN Layers. <i>Semiconductors</i> , 2018 , 52, 789-796	0.7	5
144	AlN/GaN heterostructures for normally-off transistors. <i>Semiconductors</i> , 2017 , 51, 379-386	0.7	4
143	Negative Differential Resistance Observation and a New Fitting Model for Electron Drift Velocity in GaN-Based Heterostructures. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 950-956	2.9	4
142	Increasing Saturated Electron-Drift Velocity in Donor-Acceptor Doped pHEMT Heterostructures. <i>Technical Physics Letters</i> , 2018 , 44, 260-262	0.7	4
141	About the nature of the barrier inhomogeneities at Au/Ti/n-InAlAs(001) Schottky contacts. <i>Applied Physics Letters</i> , 2019 , 114, 221602	3.4	4
140	Self-assembled Quantum Dots: From Stranski-Krastanov to Droplet Epitaxy 2012 , 127-200		4

139	Influence of shape of GaN/AlN quantum dots on luminescence decay law. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 653-656	1.6	4
138	Quantization of the electronic spectrum and localization of electrons and holes in silicon quantum dots. <i>Physics of the Solid State</i> , 2011 , 53, 860-863	0.8	4
137	Properties of manganese-doped gallium arsenide layers grown by liquid-phase epitaxy from a bismuth melt. <i>Semiconductors</i> , 1998 , 32, 704-710	0.7	4
136	Investigation of multilayer silicon structures with buried iron silicide nanocrystallites: growth, structure, and properties. <i>Journal of Nanoscience and Nanotechnology</i> , 2008 , 8, 527-34	1.3	4
135	Application of XAFS spectroscopy to studying the microstructure and electronic structure of quantum dots. <i>Journal of Surface Investigation</i> , 2007 , 1, 26-34	0.5	4
134	Photoluminescence of germanium quantum dots grown in silicon on a SiO ₂ submonolayer. <i>Physics of the Solid State</i> , 2005 , 47, 82	0.8	4
133	Photoelectric characteristics of focal plane arrays based on epitaxial layers of indium antimonide deposited on a heavily doped substrate. <i>Journal of Communications Technology and Electronics</i> , 2017 , 62, 309-313	0.5	3
132	Undoped High-Resistance GaN Buffer Layer for AlGaIn/GaN High-Electron-Mobility Transistors. <i>Technical Physics Letters</i> , 2019 , 45, 761-764	0.7	3
131	Identification of photoluminescence bands in AlGaAs/InGaAs/GaAs PHEMT heterostructures with donor-acceptor-doped barriers. <i>Semiconductors</i> , 2015 , 49, 224-228	0.7	3
130	MBE-grown AlGaIn/GaN heterostructures for UV photodetectors. <i>Technical Physics</i> , 2015 , 60, 546-552	0.5	3
129	Indium-Assisted Plasma-Enhanced Low-Temperature Growth of Silicon Oxide Nanowires. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1700749	1.6	3
128	Tunneling transport through passivated CdS nanocrystal arrays grown by the Langmuir-Blodgett method. <i>Semiconductors</i> , 2014 , 48, 1205-1210	0.7	3
127	Defects and stresses in MBE-grown GaN and Al _{0.3} Ga _{0.7} N layers doped by silicon using silane. <i>Crystallography Reports</i> , 2013 , 58, 1023-1029	0.6	3
126	An X-ray spectroscopy study of CdS nanoparticles formed by the Langmuir-Blodgett technique on the surface of carbon nanotube arrays. <i>Journal of Structural Chemistry</i> , 2017 , 58, 876-884	0.9	3
125	INFRARED PHOTOLUMINESCENCE SPECTRA OF PBS NANOPARTICLES PREPARED BY LANGMUIR-BLODGETT AND LASER ABLATION METHODS. <i>Acta Polytechnica</i> , 2014 , 54, 426-429	1	3
124	Photoluminescence of CdS nanoparticles grown on carbon nanotubes covered by a dielectric polymer layer. <i>Physica Status Solidi (B): Basic Research</i> , 2013 , 250, 2759-2764	1.3	3
123	Nonradiative recombination in GaN quantum dots formed in the AlN matrix. <i>Semiconductors</i> , 2009 , 43, 768-774	0.7	3
122	Reversal of spin polarization direction in excitonic photoluminescence of AlGaAs. <i>Europhysics Letters</i> , 2009 , 88, 17001	1.6	3

121	Microstructure of quantum dots ensembles by EXAFS spectroscopy. <i>Journal of Physics: Conference Series</i> , 2009 , 190, 012131	0.3	3
120	Mobile line in the acceptor photoluminescence spectrum of pure GaAs. <i>JETP Letters</i> , 1997 , 65, 86-90	1.2	3
119	Continuous order-disorder phase transition (2D)→(1D) on the (0001)AlN surface. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 2498-2501		3
118	Morphological, structural and luminescence properties of Si/FeSi ₂ /Si heterostructures fabricated by Fe ion implantation and Si MBE. <i>Journal Physics D: Applied Physics</i> , 2007 , 40, 5319-5326	3	3
117	Porous-like silicon prepared from Si:H annealed at high argon pressure. <i>Physica Status Solidi A</i> , 2003 , 197, 236-240		3
116	Normally off transistors based on in situ passivated AlN/GaN heterostructures. <i>Technical Physics Letters</i> , 2016 , 42, 750-753	0.7	3
115	Radiation enhancement in doped AlGaN-structures upon optical pumping. <i>Technical Physics Letters</i> , 2017 , 43, 46-49	0.7	2
114	Electronic excitation transfer from an organic matrix to CdS nanocrystals produced by the Langmuir-Blodgett method. <i>Semiconductors</i> , 2017 , 51, 576-581	0.7	2
113	Nature of intensive defect-related broadband luminescence of heavily doped Al _x Ga _{1-x} N:Si layers. <i>Journal of Physics: Conference Series</i> , 2017 , 816, 012002	0.3	2
112	Nitridation of an unreconstructed and reconstructed (111)R(0001) sapphire surface in an ammonia flow. <i>Semiconductors</i> , 2015 , 49, 905-910	0.7	2
111	Adjusting the position of the optimum operating point of a power heterostructure field-effect transistor by forming a gate potential barrier based on a donor-acceptor structure. <i>Technical Physics Letters</i> , 2015 , 41, 142-145	0.7	2
110	Minority carrier diffusion length in Al _x Ga _{1-x} N (x = 0.1) grown by ammonia molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 447-450		2
109	Surface polariton spectroscopy of AlN films grown by ammonia MBE on (0001) Al ₂ O ₃ substrate. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 439-442		2
108	Determination of the energy structure of recombination centers in heavily doped Al _x Ga _{1-x} N:Si epitaxial layers with x > 0.5. <i>Journal of Physics: Conference Series</i> , 2018 , 993, 012006	0.3	2
107	Peculiarities of CdS nanocrystal formation at annealing of a Langmuir-Blodgett matrix. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 417-420		2
106	The influence of water-organic solvent composition on the morphology and luminescent properties of CdS nanoparticles obtained by chemical precipitation. <i>Colloid Journal</i> , 2016 , 78, 30-36	1.1	2
105	Mobility of the Two-Dimensional Electron Gas in DA-pHEMT Heterostructures with Various B-Layer Profile Widths. <i>Semiconductors</i> , 2018 , 52, 44-52	0.7	2
104	Defect-related luminescence in InAlAs on InP grown by molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , 2017 , 32, 095009	1.8	2

103	MBE-grown InSb photodetector arrays. <i>Technical Physics</i> , 2017 , 62, 915-919	0.5	2
102	Diffusion and deformations in heterosystems with GaN/AlN superlattices, according to data from EXAFS spectroscopy. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2013 , 77, 1147-1150	0.4	2
101	Trapping of charge carriers into InAs/AlAs quantum dots at liquid-helium temperature. <i>Semiconductors</i> , 2011 , 45, 179-187	0.7	2
100	Interaction of excitons with carriers accelerated by the electric field of a surface acoustic wave in type-II GaAs/AlAs superlattices. <i>Physical Review B</i> , 2012 , 86,	3.3	2
99	Donor-acceptor recombination in type-II GaAs/AlAs superlattices. <i>Physics of the Solid State</i> , 1998 , 40, 1577-1581	0.8	2
98	Effect of electric field on recombination of self-trapped excitons in silicon nanocrystals. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 382-384		2
97	Exciton recombination in doped type-II GaAs/AlAs superlattices. <i>Semiconductors</i> , 2002 , 36, 461-465	0.7	2
96	Study of photoluminescence of SiO _x N _y films implanted with Ge ⁺ ions and annealed under the conditions of hydrostatic pressure. <i>Semiconductors</i> , 2001 , 35, 125-131	0.7	2
95	New impurity-induced defect in heavily zinc-doped GaAs grown by liquid phase epitaxy. <i>Semiconductor Science and Technology</i> , 1998 , 13, 1123-1129	1.8	2
94	Deep levels and electron transport in AlGa _x N/GaN heterostructures 2010 , 42, 52		2
93	Crystal Structure and Predominant Defects in CdS Quantum Dots Fabricated by the Langmuir-Blodgett Method. <i>Langmuir</i> , 2021 , 37, 5651-5658	4	2
92	Substitution of Phosphorus at the InP(001) Surface Upon Annealing in an Arsenic Flux. <i>Semiconductors</i> , 2021 , 55, 823-827	0.7	2
91	Optical Gain in Heavily Doped Al _x Ga _{1-x} N:Si Structures. <i>Technical Physics Letters</i> , 2019 , 45, 951-954	0.7	1
90	Moving photoluminescence band in AlGa _x N/GaN heterostructures. <i>Semiconductor Science and Technology</i> , 2015 , 30, 085010	1.8	1
89	AlInSb/InSb Heterostructures for IR Photodetectors Grown by Molecular-Beam Epitaxy. <i>Technical Physics Letters</i> , 2020 , 46, 154-157	0.7	1
88	Change in the Character of Biaxial Stresses with an Increase in x from 0 to 0.7 in Al _x Ga _{1-x} N:Si Layers Obtained by Ammonia Molecular Beam Epitaxy. <i>Semiconductors</i> , 2018 , 52, 221-225	0.7	1
87	Influence of defects on the photoluminescence kinetics in GaN/AlN quantum-dot structures. <i>Semiconductors</i> , 2016 , 50, 191-194	0.7	1
86	Surface Polaritons in Silicon-Doped Aluminum and Gallium Nitride Films. <i>Optics and Spectroscopy (English Translation of Optika i Spektroskopiya)</i> , 2019 , 127, 36-39	0.7	1

85	Effect of annealing and nitridation on (0001) sapphire surface polaritons. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 377-380		1
84	Original method of GaN and InGaN quantum dots formation on (0001)AlN surface by ammonia molecular beam epitaxy. <i>Journal of Physics: Conference Series</i> , 2017 , 864, 012007	0.3	1
83	The microstructure of vertically coupled quantum dots ensembles by EXAFS spectroscopy. <i>Journal of Surface Investigation</i> , 2011 , 5, 856-862	0.5	1
82	Linearly polarized photoluminescence from an ensemble of wurtzite GaN/AlN quantum dots. <i>JETP Letters</i> , 2010 , 91, 452-454	1.2	1
81	Materials for photodetectors based on intersubband transitions in GaN/AlGaIn quantum dots. <i>Journal of Optical Technology (A Translation of Opticheskii Zhurnal)</i> , 2009 , 76, 791	0.9	1
80	Recombination of charge carriers in the GaAs-based p-i-n diode. <i>Semiconductors</i> , 2010 , 44, 1362-1364	0.7	1
79	Linear polarized photoluminescence from GaN quantum dots imbedded in AlN matrix. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 2227-2229		1
78	Annihilation of nonradiative recombination centers in GaAs/AlGaAs multiquantum well structures as a result of exposure to plasma. <i>Semiconductors</i> , 1997 , 31, 1241-1243	0.7	1
77	A suite of experimental conditions for photoluminescence monitoring of a heterojunction bipolar transistor structure. <i>Technical Physics</i> , 1997 , 42, 1395-1399	0.5	1
76	Transformation of nonradiative recombination centers in GaAs/AlGaAs quantum well structures upon treatment in a CF ₄ plasma followed by low-temperature annealing. <i>Semiconductors</i> , 1998 , 32, 1293-1298	0.7	1
75	Mechanism of the effect of the electric field of a surface acoustic wave on the low-temperature photoluminescence kinetics in type-II GaAs/AlAs superlattices. <i>Semiconductors</i> , 2007 , 41, 205-210	0.7	1
74	Photoluminescence of a single InAs/AlAs quantum dot. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 2528-2529		1
73	Prolonged kinetics of photoluminescence of two-dimensional electron gas in AlGaIn/GaN heterostructure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 2095-2098		1
72	Temperature dependence of photoluminescence from CdS nanoclusters formed in the matrix of Langmuir-Blodgett film. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 3951-3954		1
71	Exciton fine structure and spin dynamics in high purity AlGaAs layers. <i>Semiconductor Science and Technology</i> , 2004 , 19, S377-S379	1.8	1
70	Effect of uniform compression on photoluminescence spectra of GaAs layers heavily doped with beryllium. <i>Semiconductors</i> , 2004 , 38, 277-280	0.7	1
69	Growth kinetics of (0001)GaN from Ga and NH ₃ fluxes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004 , 1, 325-328		1
68	Optically detected magnetic resonance of shallow donors in GaAs observed in photoluminescence kinetics. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 669-672		1

67	Properties of Ge nanocrystals formed by implantation of Ge ⁺ ions into SiO ₂ films with subsequent annealing under hydrostatic pressure. <i>Semiconductors</i> , 2003 , 37, 462-467	0.7	1
66	Observation of exchange interaction effects under optical orientation of excitons in AlGaAs. <i>JETP Letters</i> , 2003 , 77, 561-564	1.2	1
65	Photoluminescence kinetics of wurtzite GaN quantum dots in an AlN matrix. <i>JETP Letters</i> , 2005 , 81, 62-65.2	1.2	1
64	Photoluminescence of silicon nanocrystals under the effect of an electric field. <i>Semiconductors</i> , 2005 , 39, 1319	0.7	1
63	Polariton luminescence in high-purity layers of AlGaAs solid solutions. <i>JETP Letters</i> , 2000 , 71, 148-150	1.2	1
62	Use of high-purity Al _x Ga _{1-x} as layers in epitaxial structures for high-power microwave field-effect transistors. <i>Technical Physics Letters</i> , 1999 , 25, 595-597	0.7	1
61	Modification of the surface energy and morphology of GaN monolayers on the AlN surface in an ammonia flow. <i>Applied Physics Letters</i> , 2022 , 120, 053101	3.4	1
60	Donor-acceptor nature of orange photoluminescence in AlN. <i>Semiconductor Science and Technology</i> , 2020 , 35, 125006	1.8	1
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